

# Jun Yamauchi

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2676769/publications.pdf>

Version: 2024-02-01

10  
papers

554  
citations

1477746

6  
h-index

1372195

10  
g-index

10  
all docs

10  
docs citations

10  
times ranked

302  
citing authors

#	ARTICLE	IF	CITATIONS
1	First-principles study on energetics of c-BN(001) reconstructed surfaces. Physical Review B, 1996, 54, 5586-5603.	1.1	460
2	Identification of boron clusters in silicon crystal by B 1s core-level X-ray photoelectron spectroscopy: A first-principles study. Applied Physics Letters, 2011, 99, .	1.5	37
3	Deactivation mechanism of In atoms doped in a Si crystal and reactivation due to codoping with B and C. Physical Review B, 2005, 71, .	1.1	14
4	X-ray photoelectron spectroscopy analysis of boron defects in silicon crystal: A first-principles study. Journal of Applied Physics, 2016, 119, .	1.1	14
5	Electronic transport properties of thin, channel regions from SOI through GOI: A first-principles study. Thin Solid Films, 2006, 508, 342-345.	0.8	12
6	First-principles X-ray photoelectron spectroscopy binding energy shift calculation for boron and aluminum defects in 3C-silicon carbide. Japanese Journal of Applied Physics, 2019, 58, 031001.	0.8	8
7	Effective Mass Anomalies in Strained-Si Thin Films and Crystals. IEEE Electron Device Letters, 2008, 29, 186-188.	2.2	4
8	Effective-Mass Anomalies of Strained Silicon Thin Films: Surface and Confinement Effects. Japanese Journal of Applied Physics, 2007, 46, 3273-3276.	0.8	2
9	First-principles calculation of X-ray photoelectron spectroscopy binding energy shift for nitrogen and phosphorus defects in 3C-silicon carbide. Japanese Journal of Applied Physics, 2019, 58, 061005.	0.8	2
10	Core-level shifts in x-ray photoelectron spectroscopy of arsenic defects in silicon crystal: A first-principles study. AIP Advances, 2020, 10, 115301.	0.6	1